

Features

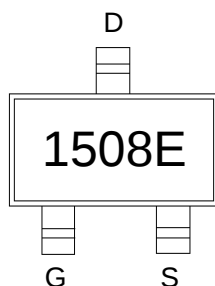
- High dense cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- ESD Protected Gate

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
15V	7.7mΩ@4.5V	8A
	8.6mΩ@2.5V	

Application

- Load/Power Switching

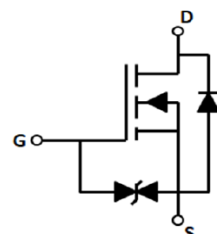


1508E: Device code

Marking and pin assignment



SOT-23-3L top view



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

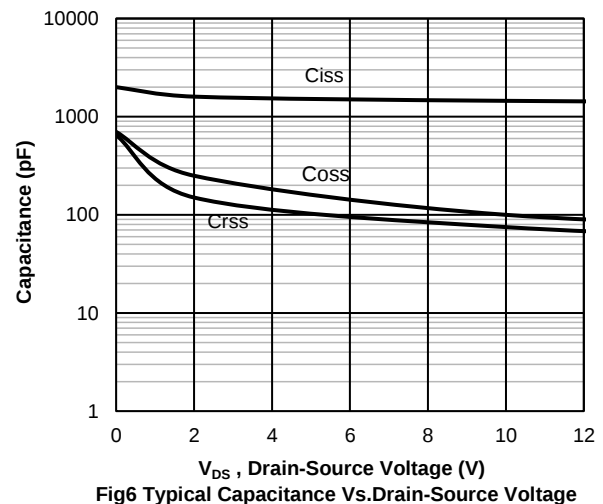
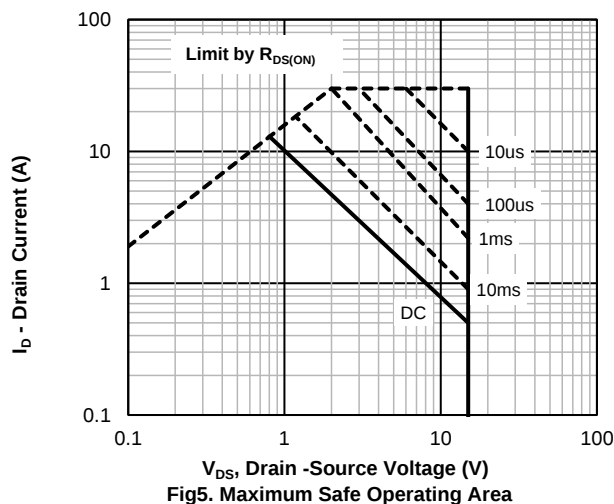
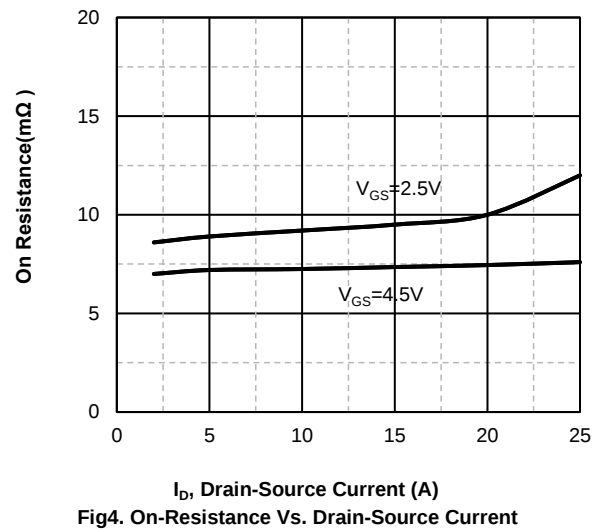
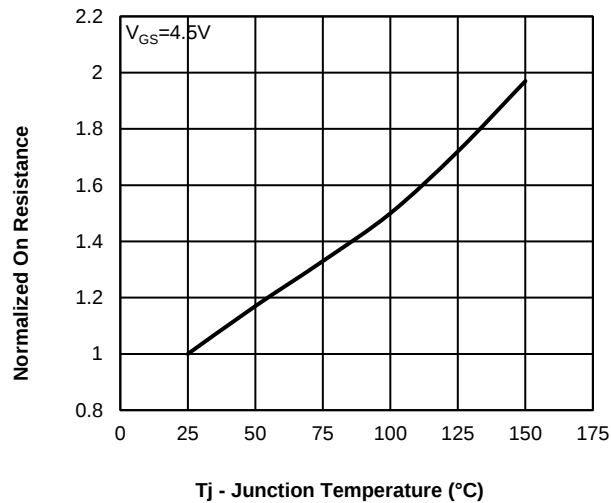
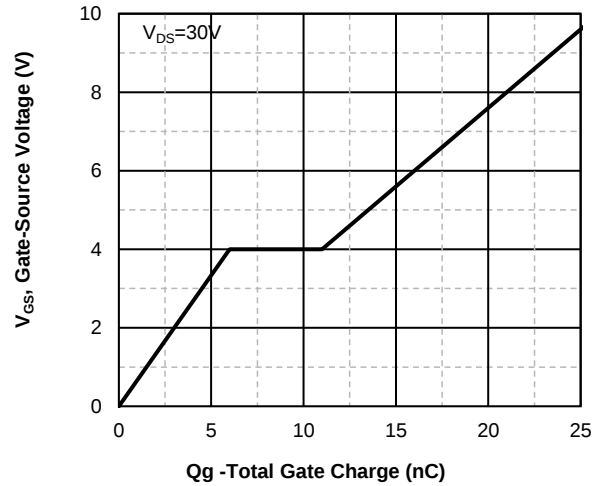
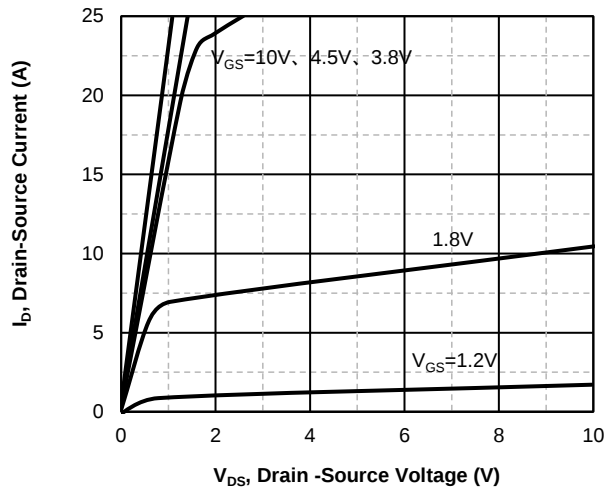
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{DS}	Drain-Source Breakdown Voltage		15	V
V _{GS}	Gate-Source Voltage		±12	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	8	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	Tc=25°C	30	A
I _D	Continuous Drain Current	Tc=25°C	8	A
P _D	Maximum Power Dissipation	Tc=25°C	0.5	W
R _{θJA}	Thermal Resistance Junction-Ambient		249	°C/W

Ordering Information (Example)

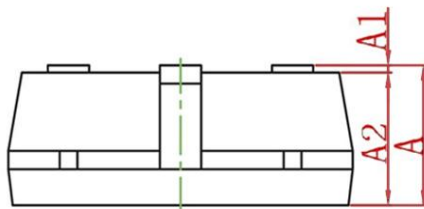
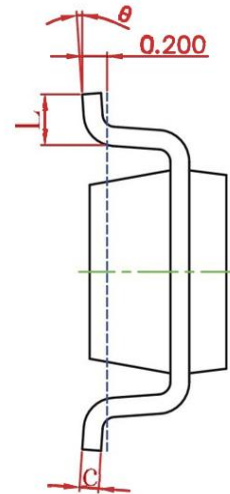
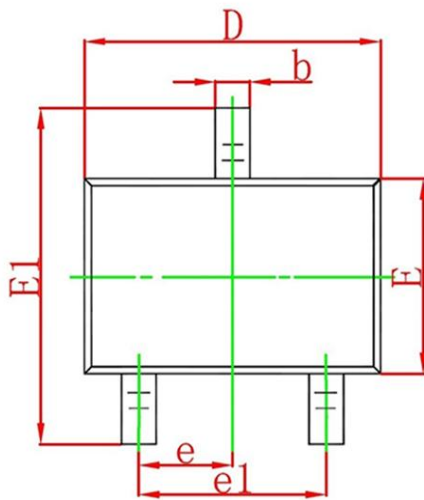
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSK1508E	SOT-23-3L	1508E	3,000	45,000	180,000	7" reel

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	15	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =15V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±10	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	--	1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =3A	--	7.7	9.5	mΩ
		V _{GS} =2.5V, I _D =3A	--	8.6	10.5	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	1500	--	pF
C _{OSS}	Output Capacitance		--	100	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	70	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =10V, I _D =3A, V _{GS} =4.5V	--	17.9	--	nC
Q _{gs}	Gate Source Charge		--	1.5	--	nC
Q _{gd}	Gate Drain Charge		--	4.7	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =10V, I _D =3A, V _{GS} =10V, R _G =3Ω	--	2.5	--	nS
t _r	Turn-on Rise Time		--	7.2	--	nS
t _{d(off)}	Turn-Off Delay Time		--	49	--	nS
t _f	Turn-Off Fall Time		--	10.8	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25℃, Is=8A	--	--	1.2	V

Typical Operating Characteristics



SOT-23-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.042	0.050
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.042	0.046
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.112	0.120
E	1.500	1.700	0.060	0.068
E1	2.650	2.950	0.106	0.118
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°